FM25160

16Kb FRAM Serial Memory

Features

16K bit Ferroelectric Nonvolatile RAM

- Organized as 2,048 x 8 bits
- High Endurance 10 Billion (10^{10}) Read/Writes
- 10 Year Data Retention
- NoDelay™ Writes
- Advanced High-Reliability Ferroelectric Process

Fast Serial Peripheral Interface - SPI

- Up to 1.8 MHz maximum bus frequency
- Direct hardware replacement for EEPROM
- Supports SPI Mode 0 (CPOL=0, CPHA=0)

Sophisticated Write Protection Scheme

- Hardware Protection
- Software Protection

Low Power Consumption

- 10 µA Standby Current

Industry Standard Configuration

- Industrial Temperature -40° C to +85° C
- 8-pin SOIC or PDIP

Description

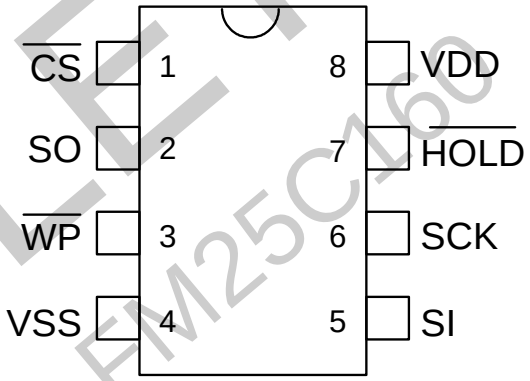
The FM25160 is a 16-kilobit nonvolatile memory employing an advanced ferroelectric process. A ferroelectric random access memory or FRAM is nonvolatile and performs reads and writes like a RAM. It provides reliable data retention for 10 years while eliminating the complexities, overhead, and system level reliability problems caused by EEPROM and other nonvolatile memories.

Unlike serial EEPROMs, the FM25160 performs write operations at bus speed. No write delays are incurred. Data is written to the memory array in the cycle after it has been successfully transferred to the device. The next bus cycle may commence immediately. The FM25160 is capable of supporting 10^{10} read/write cycles, or 10,000 times more write cycles than EEPROM.

These capabilities make the FM25160 ideal for nonvolatile memory applications requiring frequent or rapid writes. Examples range from data collection, where the number of write cycles may be critical, to demanding industrial controls where the long write time of EEPROM can cause data loss.

The FM25160 provides substantial benefits to users of serial EEPROM, in a hardware drop-in replacement. The FM25160 uses the high-speed SPI bus, which enhances the high-speed write capability of FRAM technology. The specifications are guaranteed over an industrial temperature range of -40°C to +85°C.

Pin Configuration



Pin Names	Function
/CS	Chip Select
/WP	Write Protect
/HOLD	Hold
SCK	Serial Clock
SI	Serial Data Input
SO	Serial Data Output
VDD	Supply Voltage 5V
VSS	Ground

Ordering Information	
FM25160-P	8-pin plastic PDIP
FM25160-S	8-pin SOIC

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1850 Ramtron Drive, Colorado Springs, CO 80921
(800) 545-FRAM, (719) 481-7000
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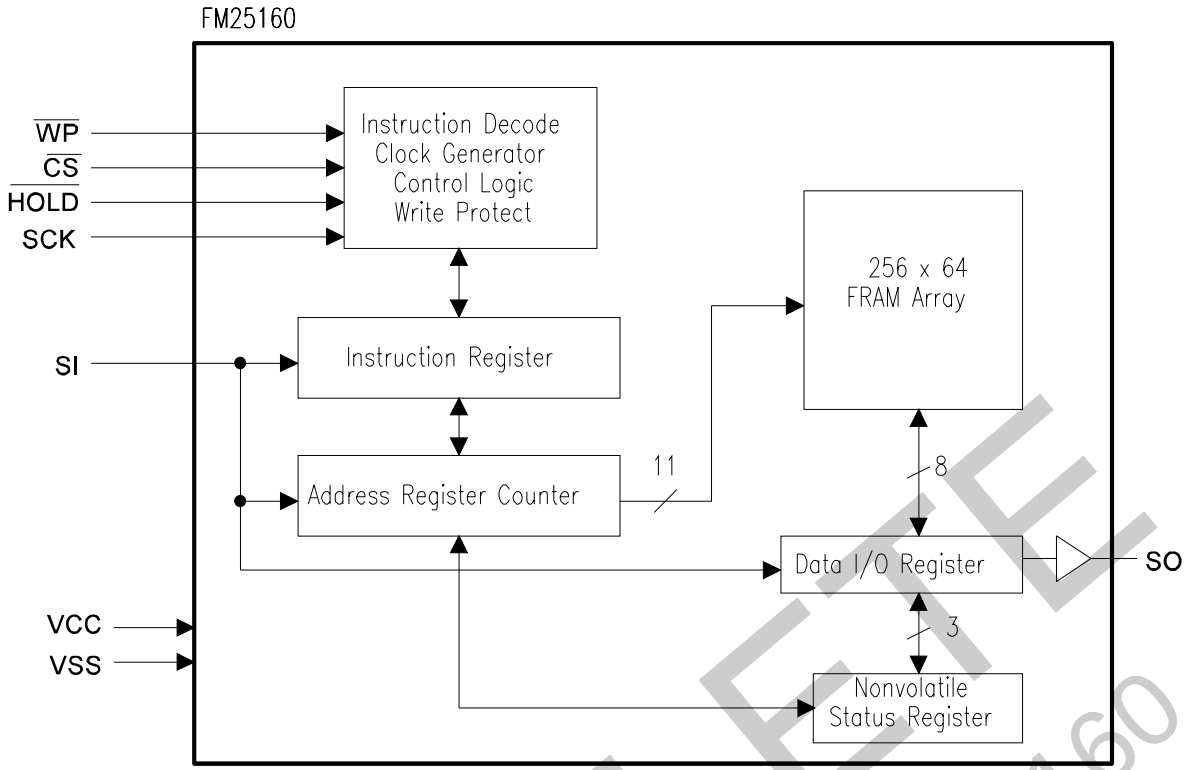


Figure 1. Block Diagram

Pin Descriptions

Pin Name	I/O	Description
/CS	Input	Chip Select. This active-low input activates the device. When high, the device enters low-power standby mode, ignores other inputs, and all outputs are tri-stated. When low, the device internally activates the SCK signal. A falling edge on /CS must occur prior to every op-code.
SCK	Input	Serial Clock. All I/O activity is synchronized to the serial clock. Inputs are latched on the rising edge and outputs occur on the falling edge. Because the device is static, the clock frequency may be any value between 0 and 1.8 MHz and may be interrupted at any time.
/HOLD	Input	Hold. The /HOLD pin is used when the host CPU must interrupt a memory operation for another task. When /HOLD is low, the current operation is suspended. The device ignores any transition on SCK or /CS. All transitions on /HOLD must occur while SCK is low.
/WP	Input	Write Protect. This active low input prevents write operations to the status register. This is critical since many other write protection features are controlled through the status register. A complete explanation of write protection is provided on page 6. Note that the function of /WP is different from the FM25040 where it prevent all writes to the part.
SI	Input	Serial Input. All data is input to the device on this pin. The pin is sampled on the rising edge of SCK and is ignored at other times. It should always be driven to a valid logic level to meet I_{DD} specifications. * SI may be connected to SO for a single pin data interface.
SO	Output	Serial Output. SO is the data output pin. It is driven actively during a read and remains tri-state at all other times including when /HOLD is low. Data transitions are driven on the falling edge of the serial clock. * SO can be connected to SI for a single pin data interface since the part communicates in half-duplex fashion.
VDD	I	Supply Voltage: 5V
VSS	I	Ground

Overview

The FM25160 is a serial FRAM memory. The memory array is logically organized as 2,048 x 8 and is accessed using an industry standard Serial Peripheral Interface or SPI bus. Functional operation of the FRAM is similar to serial EEPROMs. The major difference between the FM25160 and a serial EEPROM with the same pinout relates to its superior write performance.

Memory Architecture

When accessing the FM25160, the user addresses 2,048 locations each with 8 data bits. These data bits are shifted serially. The addresses are accessed using the SPI protocol, which includes a chip select (to permit multiple devices on the bus), an op-code including a page address, and a word address. The word address consists of 8-bits that specify one of 256 addresses. The page address is 3-bits and so there are 8 pages each of 256 locations. The complete address of 11-bits specifies each byte address uniquely.

Most functions of the FM25160 are either controlled by the SPI interface or are handled automatically by on-board circuitry. The memory is read or written at the speed of the SPI bus. Unlike an EEPROM, it is not necessary to poll the device for a ready condition since writes occur at bus speed. That is, by the time a new bus transaction can be shifted into the part, a write operation will be complete. This is explained in more detail in the interface section below.

Users can expect several system benefits from the FM25160 due to its fast write cycle and high endurance as compared with EEPROM. However there are less obvious benefits as well. For example in a high noise environment, the fast-write operation is less susceptible to corruption than an EEPROM since it is completed quickly. By contrast an EEPROM requiring milliseconds to write is vulnerable to noise during much of the cycle.

Note that the FM25160 contains no power management circuits other than a simple internal power-on reset. It is the user's responsibility to ensure that VDD is within data sheet tolerances to prevent incorrect operation.

Serial Peripheral Interface – SPI Bus

The FM25160 employs a Serial Peripheral Interface (SPI) bus. This high-speed serial bus provides high performance serial communication to a host microcontroller. Many common microcontrollers have hardware SPI ports which allow a direct interface to the FM25160. For microcontrollers that do not have a SPI bus, it is relatively easy to emulate the port using ordinary port pins.

The SPI interface uses a total of four pins: chip select, clock, data-in, and data-out. It is possible to achieve a 3-wire interface by connecting the two data lines together. Figure 2 illustrates a typical system configuration using the FM25160 with a microcontroller that has a SPI port. Figure 3 shows a similar configuration for a microcontroller that has no hardware support for the SPI bus.

Protocol Overview

The SPI interface is a synchronous serial interface that uses a chip select, a clock, and two data lines. The bus was designed to support multiple devices on the bus by using a chip select per device. Each device is activated using a chip select. Once chip select is asserted by the bus master, the FM25160 will begin monitoring the clock and data lines. The relationship between the falling edge of /CS, the clock, and data is dictated by the SPI mode. There are four such modes, however the FM25160 supports only mode 0. This mode dictates that the SCK signal must be low when /CS is activated.

The SPI protocol is controlled by op-codes. These op-codes specify the commands to the part. After /CS is asserted, the first byte transferred from the bus master is the op-code. Following the op-code, addresses and data are then transferred.
Certain op-codes are commands with no subsequent data transfer. The /CS must go inactive after an operation is complete and before a new op-code can be issued.

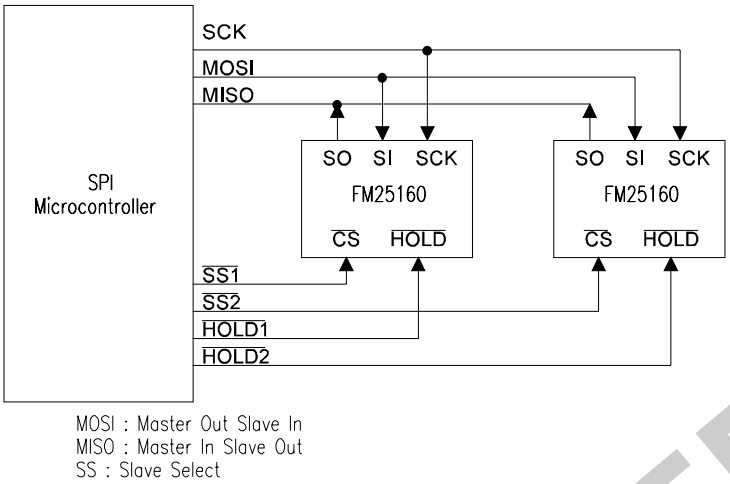


Figure 2. System Configuration with SPI port

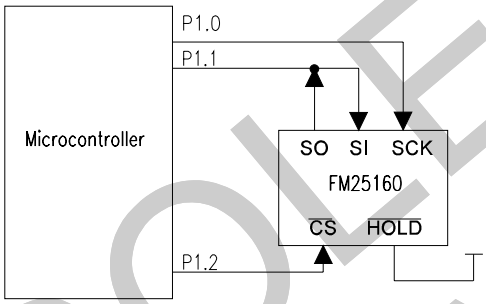


Figure 3. System Configuration without SPI port

Data Transfer

All data transfers to and from the FM25160 occur in 8-bit groups. They are synchronized to the clock signal (SCK) and occur most significant bit (MSB) first. Serial input data is clocked into the device on the rising edge of SCK. Serial output data is driven on the falling edge of SCK.

Command Structure

There are six commands called op-codes that can be issued by the bus master to the FM25160. These op-codes control the functions performed by the memory. They can be divided into three categories. First, there are commands that have no subsequent data operations. They perform a single task such as enabling or disabling a write operation. In the second category are commands that initiate a single-byte operation. These operate on the status register. Third, there are commands for memory transactions that require an address and one or more bytes of data.

Table 1. Op-code Commands

Name	Description	Op-code
WREN	Set Write Enable Latch	0000 0110b
WRDI	Write Disable	0000 0100b
RDSR	Read Status Register	0000 0101b
WRSR	Write Status Register	0000 0001b
READ	Read Memory Data	00AA A011b
WRITE	Write Memory Data	00AA A010b

WREN - Set Write Enable Latch

The FM25160 will power up with write capability disabled. The WREN command must be issued prior to any write operation. Sending the WREN op-code will allow the user to issue subsequent op-codes for write operations. These include writing the status register and writing the memory.

Sending the WREN op-code causes the internal Write Enable Latch to be set. A flag bit in the status register called WEL indicates the state of the latch. WEL=1 indicates that writes are permitted. Since the WEL bit in the status register is read-only, the user cannot write the WEL bit. Completing any write operation will automatically clear the write enable latch and prevent further writes without another WREN command. Figure 4 illustrates the WREN command bus configuration.

WRDI - Write Disable

The WRDI command disables all write activity by clearing the Write Enable Latch. The user can verify that writes are disabled by reading the WEL bit in the status register and verifying that WEL=0. Figure 5 below illustrates the WRDI command bus configuration.

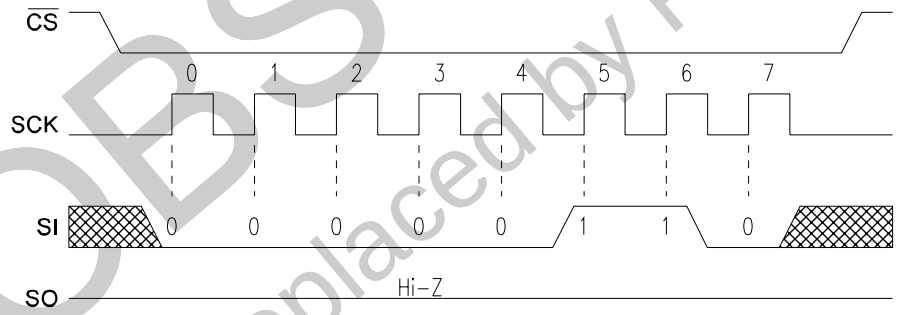


Figure 4. WREN Bus Configuration

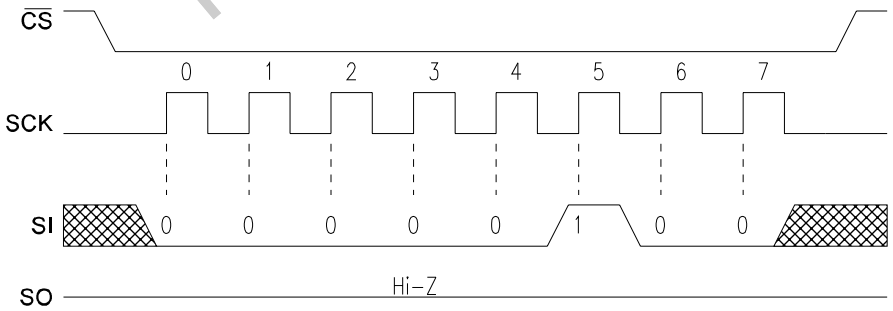


Figure 5. WRDI Bus Configuration

RDSR - Read Status Register

The RDSR command allows the bus master to verify the contents of the Status register. Reading Status provides information about the current state of the write protection features. Following the RDSR op-code, the FM25160 will return one byte with the contents of the Status register. The Status register is described in detail in a later section.

WRSR – Write Status Register

The WRSR command allows the user to select certain write protection features by writing a byte to the Status register. Prior to issuing a WRSR command, the /WP pin must be high or inactive. Note that on the FM25160, /WP prevents writing to the Status register and the memory array. Also prior to sending the WRSR command, the user must send a WREN command to enable writes. Note that executing a WRSR command is a write operation and therefore clears the Write Enable Latch. The bus configuration of RDSR and WRSR are shown below.

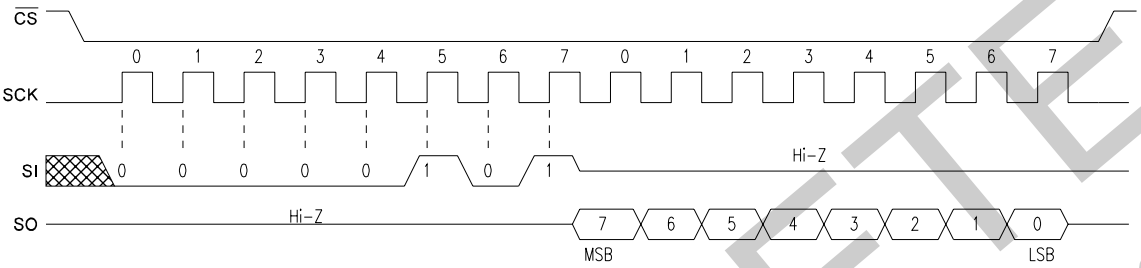


Figure 6. RDSR Bus Configuration

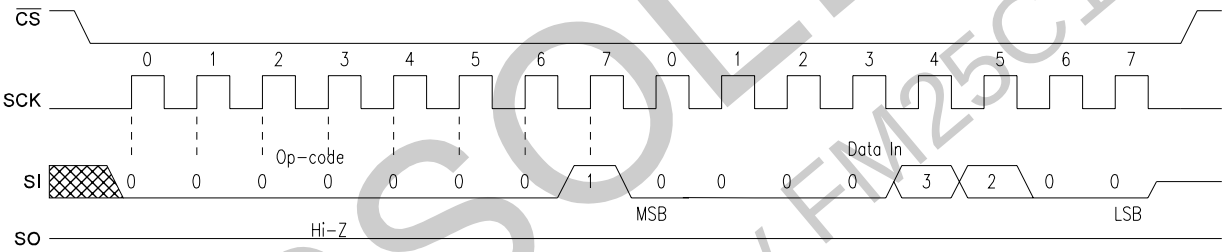


Figure 7. WRSR Bus Configuration

Status Register & Write Protection

The write protection features of the FM25160 are relatively simple to use. First, a WREN op-code must be issued prior to any write operation. Assuming that writes are enabled using WREN, writes to memory are controlled by the /WP pin and the Status register. When /WP is low, the entire part is write-protected. When /WP is high, the memory protection is subject to the Status register. As described above, writes to the status register are performed using the WRSR command and are subject to the /WP pin. The Status register is organized as follows.

Table 2. Status Register

Bit	7	6	5	4	3	2	1	0
Name	WPEN	0	0	0	BP1	BP0	WEL	0

Bits 0 and 4-6 are fixed at 0 and cannot be modified. Note that bit 0 (/RDY in EEPROMs) is wired low since FRAM writes have no delay and the memory is never busy. All EEPROMs use Ready to indicate whether a write cycle is complete or not. The WEL flag indicates the state of the Write Enable Latch. This bit is internally set by the WREN command and is cleared by terminating a write cycle (/CS high) or by using the WRDI command. The nonvolatile BP1 and BP0 bits are memory block write-protection bits. They specify portions of memory that are write-protected as shown below.

Table 3. Block Memory Write Protection

BP1	BP0	Protected Address Range
0	0	None
0	1	600h to 7FFh (upper ¼)
1	0	400h to 7FFH (upper ½)
1	1	000h to 7FFh (all)

The BP1 and BP0 bits protect selected portions of the memory array from writes. The /WP pin and Write Enable Latch protect the entire part including the BP bits. The following table summarizes the write protection conditions.

Table 4. Write Protection

WEL	WPEN	/WP	Protected Memory Blocks	Unprotected Memory Blocks	Status Register
0	X	X	Protected	Protected	Protected
1	0	X	Protected	Unprotected	Unprotected
1	1	0	Protected	Unprotected	Protected
1	1	1	Protected	Unprotected	Unprotected

Memory Operation

The SPI interface, with its relatively high maximum clock frequency, highlights the fast write capability of the FRAM technology. Unlike SPI bus EEPROMs the FM25160 can perform sequential writes at bus speed. No page register is needed and any number of sequential writes may be performed.

Write Operation

All writes to the memory array begin with a WREN op-code. The bus master then issues a WRITE op-code. Part of this op-code includes the upper 3-bits of the memory address. Bits 5, 4, and 3 in the op-code correspond to A10, A9, A8, respectively. The next byte is the lower 8-bits of the address. In total, the 11-bits specify the address of the first byte of the write operation. Subsequent bytes are data and they are written sequentially. Addresses are incremented internally as long as the bus master continues to issue clocks while /CS is low. If the last address 7FFh is reached, the counter will roll over to 000h. Data is written MSB first.

Unlike EEPROMs, any number of bytes can be written sequentially and each byte is written to memory immediately after it is clocked in (after the 8th clock). The rising edge of /CS terminates a WRITE op-code operation.

Read Operation

After the falling edge of /CS, the bus master can issue a READ op-code. Part of this op-code includes the upper 3-bits of the memory address. The next byte is the lower 8-bits of the address. In total, the 11-bits specify the address of the first byte of the read operation. After the op-code is complete, the SI line is ignored. The bus master then issues 8 clocks, with one bit read out for each. Addresses are incremented internally as long as the bus master continues to issue clocks. If the last address 7FFh is reached, the counter will roll over to 000h. Data is read MSB first. The rising edge of /CS terminates a READ op-code operation. The bus configuration for read and write operations is shown below.

Hold

The /HOLD pin can be used to interrupt a serial operation without aborting it. If the bus master takes the /HOLD pin low while SCK is low, the current operation will pause. Taking the /HOLD pin high while SCK is low will resume an operation. The transitions of /HOLD must occur while SCK is low, but the SCK and I/O pins can toggle during a hold state. However, before removing the HOLD condition, all pins should return to their state prior to the HOLD. A diagram illustrating the HOLD timing is provided on page 12.

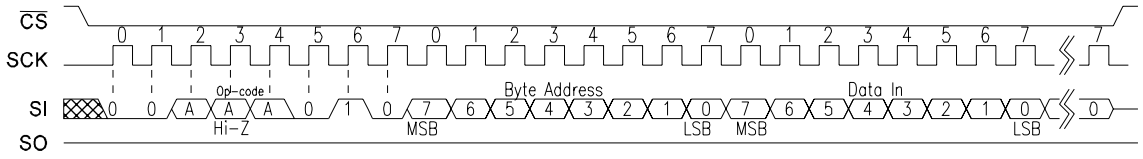


Figure 8. Memory Write

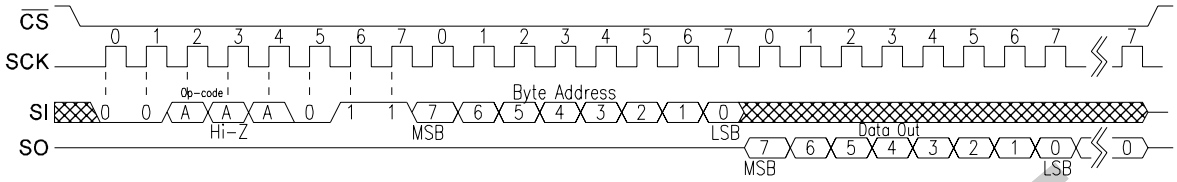


Figure 9. Memory Read

Data Retention and Endurance

Data retention is specified in the electrical specifications below. For purposes of clarity, this section contrasts the retention and endurance of FRAM with EEPROM. The retention performance of FRAM is very comparable to EEPROM in its characteristics. However, the effect of endurance cycles on retention is different.

A typical EEPROM has a write endurance specification that is fixed. Surpassing the specified level of cycles on an EEPROM usually leads to a hard memory failure. By contrast, the effect of increasing cycles on FRAM produces an increase in the soft error rate. That is, there is a higher likelihood of data loss but the memory continues to function properly. A hard failure would not occur by simply exceeding the endurance specification; simply a reduction in data retention reliability. While enough cycles would cause an apparent hard error, this is simply a very high soft error rate. This characteristic makes it problematic to assign a fixed endurance specification.

Endurance is a soft specification. Therefore, the user may operate the device with different levels of endurance cycling for different portions of the memory. For example, critical data needing the highest reliability level could be stored in memory locations that receive comparatively few cycles. Data with shorter-term use could be located in an area receiving many more cycles. A scratchpad area, needing little if any retention can be cycled until there is virtually no retention capability remaining. This would occur several orders of magnitude above the endurance spec.

Internally, a FRAM operates with a read and restore mechanism. Therefore, endurance cycles are applied for each read or write cycle. The FRAM architecture is based on an array of rows and columns. Rows are defined by A10-A3. Each access causes an endurance cycle for a row. Endurance can be optimized by ensuring frequently accessed data is located in different rows. Regardless, FRAM read and write endurance is effectively unlimited at the 1.8MHz two-wire speed. Even at 30 accesses per second to the same row, 10 years time will elapse before 10 billion endurance cycles occur.

Applications

The versatility of FRAM technology fits into many diverse applications. Clearly the strength of higher write endurance and faster writes make FRAM superior to EEPROM in all but one-time programmable applications. The advantage is most obvious in data collection environments where writes are frequent and data must be nonvolatile.

The attributes of fast writes and high write endurance combine in many innovative ways. A short list of ideas is provided here.

1. Data collection. In applications where data is collected and saved, FRAM provides a superior alternative to other solutions. It is more cost effective than battery backup for SRAM and provides better write attributes than EEPROM.

2. Configuration. Any nonvolatile memory can retain a configuration. However if the configuration changes and power failure is a possibility, the higher write endurance of FRAM allows changes to be recorded without restriction. Any time the system state is altered, the change can be written. This avoids writing to memory on power down when the available time is short and power scarce.

3. High noise environments. Writing to EEPROM in a noisy environment can be challenging. When severe noise or power fluctuations are present, the long write time of EEPROM creates a window of vulnerability during which the write can be corrupted. The fast write of FRAM is complete within a microsecond. This time is typically too short for noise or power fluctuation to disturb it.

4. Time to market. In a complex system, multiple software routines may need to access the nonvolatile memory. In this environment the time delay associated with programming EEPROM adds undue complexity to the software development. Each software routine must wait for complete programming before allowing access to the next routine. When time to market is critical, FRAM can eliminate this simple obstacle. As soon as a write is issued to the FM25160, it is effectively done -- no waiting.

5. RF/ID. In the area of contactless memory, FRAM provides an ideal solution. Since RF/ID memory is powered by an RF field, the long programming time and high current consumption needed to write EEPROM is unattractive. FRAM provides a superior solution. The FM25160 is suitable for multi-chip RF/ID products.

6. Maintenance tracking. In sophisticated systems, the operating history and system state during a failure is important knowledge. Maintenance can be expedited when this information has been recorded. Due to the high write endurance, FRAM makes an ideal system log. In addition, the convenient 2-wire interface of the FM25160 allows memory to be distributed throughout the system using minimal additional resources.

Electrical Specifications

Absolute Maximum Ratings

Symbol	Description	Ratings
V_{DD}	Power Supply Voltage with respect to V_{SS}	-1.0V to +7.0V
V_{IN}	Voltage on any pin with respect to V_{SS}	-1.0V to +7.0V and $V_{IN} < V_{DD}$+1.0V
T_{STG}	Storage Temperature	-40°C to + 85°C
T_{LEAD}	Lead Temperature (Soldering, 10 seconds)	300° C

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only, and the functional operation of the device at these or any other conditions above those listed in the operational section of this specification is not implied. Exposure to absolute maximum ratings conditions for extended periods may affect device reliability.

DC Operating Conditions (T_A = -40°C to + 85°C, VDD = 4.5V to 5.5V unless otherwise specified)

Symbol	Parameter	Min	Typ	Max	Units	Notes
V_{DD}	Main Power Supply	4.5	5.0	5.5	V	
I_{DD}	VDD Supply Current @ SCK = 1.0 MHz @ SCK = 1.8 MHz		 0.9 1.6	 1.2 2.5	 mA mA	1
I_{SB}	Standby Current		1	10	µA	2
I_{LI}	Input Leakage Current			10	µA	3
I_{LO}	Output Leakage Current			10	µA	3
V_{IH}	Input High Voltage	0.7 V_{DD}		V_{DD} + 0.5	V	
V_{IL}	Input Low Voltage	-0.3		0.3 V_{DD}	V	
V_{OH}	Output High Voltage @ I_{OH} = -1 mA	V_{DD} – 0.8		-	V	
V_{OL}	Output Low Voltage @ I_{OL} = 3 mA	-		0.4	V	
V_{HYS}	Input Hysteresis	0.05 V_{DD}		-	V	4

Notes
1. SCK toggling between VDD-0.3V and VSS, other inputs VSS or VDD-0.3V
2. SCK = SI = /CS=VDD. All inputs VSS or VDD.
3. VIN or VOUT = VSS to VDD
4. This parameter is periodically sampled and not 100% tested.

AC Parameters (T_A = -40°C to + 85°C, VDD = 4.5V to 5.5V unless otherwise specified)

Symbol	Parameter	Min	Max	Units
f_{CK}	SCK Clock Frequency	0	1.8	MHz
t_{CH}	Clock High Time	200		ns
t_{CL}	Clock Low Time	200		ns
t_{CSU}	Chip Select Setup	240		ns
t_{CSH}	Chip Select Hold	240		ns
t_{OD}	Output Disable		240	ns
t_{ODV}	Output Data Valid		200	ns
t_{OH}	Output Hold	0		ns
t_D	Deselect Time	240		ns
t_R	Data Rise Time		2.0	µS
t_F	Data Fall Time		2.0	µS
t_H	Data Hold Time	100		ns
t_{SU}	Data Setup Time	100		ns
t_{HS}	/Hold Setup Time	90		ns
t_{HH}	/Hold Hold Time	90		ns
t_{HZ}	/Hold Low to Hi-Z		100	ns
t_{LZ}	/Hold High to Data Active		100	ns

Notes
1. Rise and fall times measured between 10% and 90% of waveform.

Capacitance T_A = 25°C, f=1.0 MHz, VDD = 5V

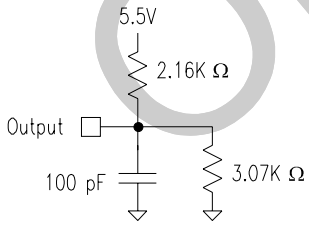
Symbol	Parameter	Max	Units	Notes
C_O	Output capacitance (SO)	8	pF	1
C_I	Input capacitance	6	pF	1

Notes
1. This parameter is periodically sampled and not 100% tested.

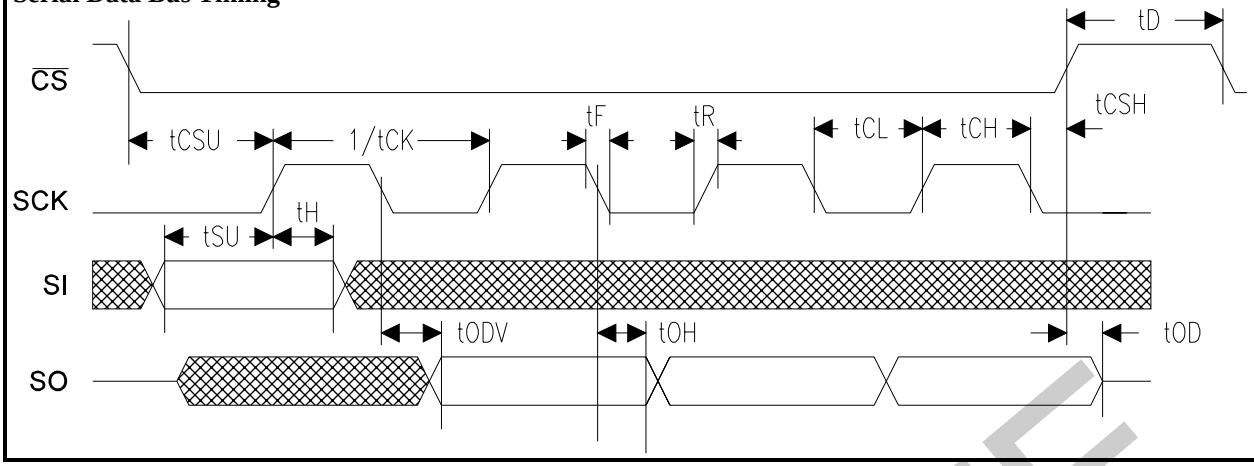
AC Test Conditions

Input Pulse Levels	10% and 90% of V_{DD}
Input rise and fall times	10 ns
Input and output timing levels	V_{DD}*0.5

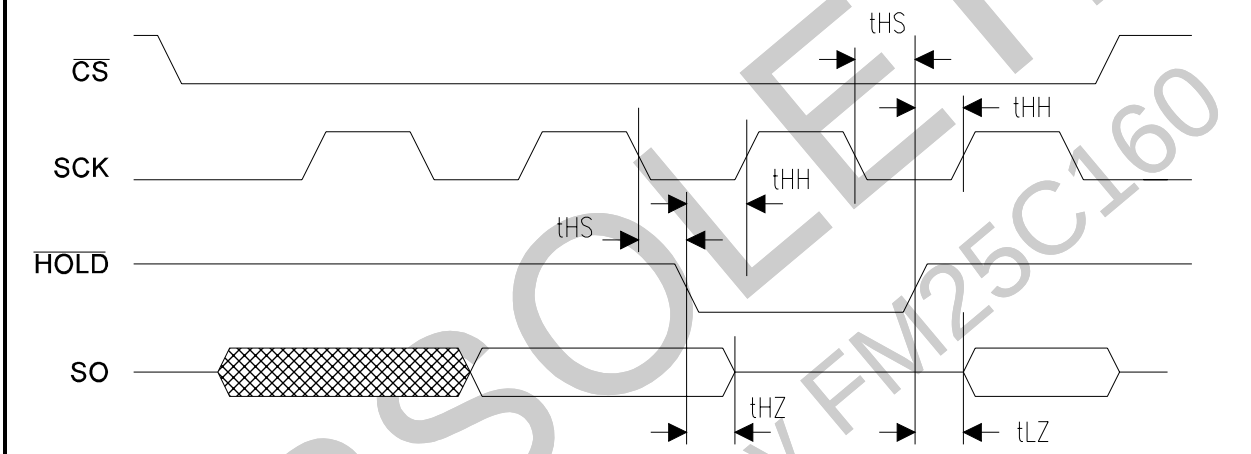
Equivalent AC Load Circuit



Serial Data Bus Timing



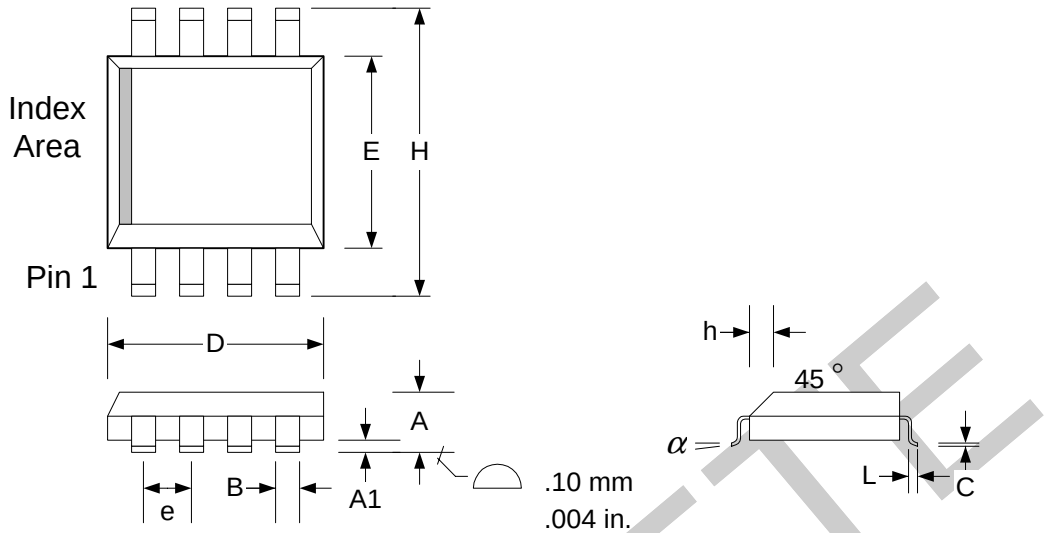
/Hold Timing



Data Retention VDD = 4.5V to 5.5V unless otherwise specified

Parameter	Min	Units	Notes
Data Retention	10	Years	1

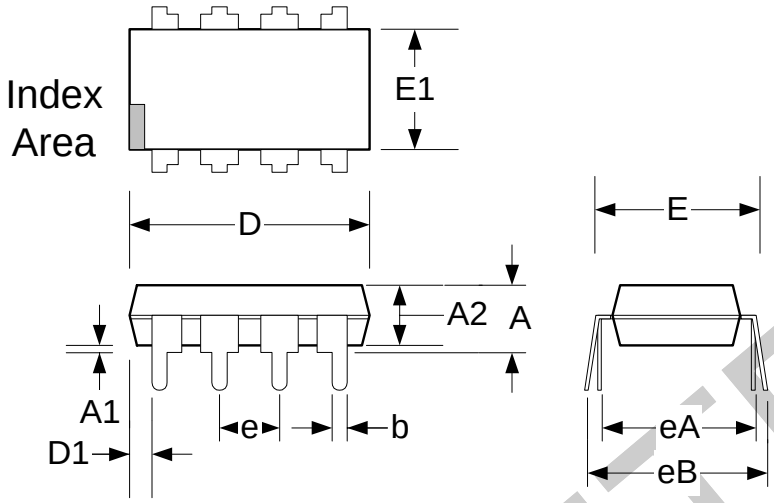
Mechanical Drawing (8-pin SOIC - JEDEC Standard MS-012)



Selected Dimensions
Refer to JEDEC MS-012 for complete dimensions and notes.
Controlling dimensions in millimeters.
Conversions to inches are not exact.

Symbol	Dim	Min	Nom.	Max
A	mm in.	1.35 .053		1.75 .069
A1	mm in.	.10 .004		.25 .010
B	mm in.	.33 .013		.51 .020
C	mm in.	.19 .007		.25 .010
D	mm in.	4.80 .189		5.00 .197
E	mm in.	3.80 .150		4.00 .157
e	mm in.		1.27 BSC .050 BSC	
H	mm in.	5.80 .228		6.20 .244
h	mm in.	.25 .010		.50 .197
L	mm in.	.40 .016		1.27 .050
α		0°		8°

Mechanical Drawing (8-pin PDIP - JEDEC Standard MS-001)



Selected Dimensions
Refer to JEDEC MS-001 for complete dimensions and notes.
Controlling dimensions in inches.
Conversions to millimeters are not exact.

Symbol	Dim	Min	Nom.	Max
A	in. mm			.210 5.33
A1	in. mm	0.015 .381		
A2	in. mm	0.115 2.92	0.130 3.30	0.195 4.95
b	in. mm	0.014 .356	0.018 .457	0.022 .508
D	in. mm	0.355 9.02	0.365 9.27	0.400 10.2
D1	in. mm	0.005 .127		
E	in. mm	0.300 7.62	0.310 7.87	0.325 8.26
E1	in. mm	0.240 6.10	0.250 6.35	0.280 7.11
e	in. mm		.100 BSC 2.54 BSC	
eA	in. mm		.300 BSC 7.62 BSC	
eB	in. mm			0.430 10.92
L	in. mm	0.115 2.92	0.130 3.30	0.150 3.81